Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	22	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

(T_j=25

TYN 80 H -1600 SJ

- TYN: SCRs
- 80: $I_{T(AV)}$:80A
- H: High junction temperature
- -1600: V_{DRM} /V_{RRM} ≥1600V
- SJ: SJ:TO-247J

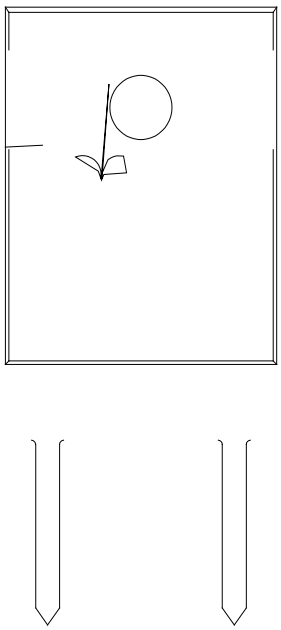
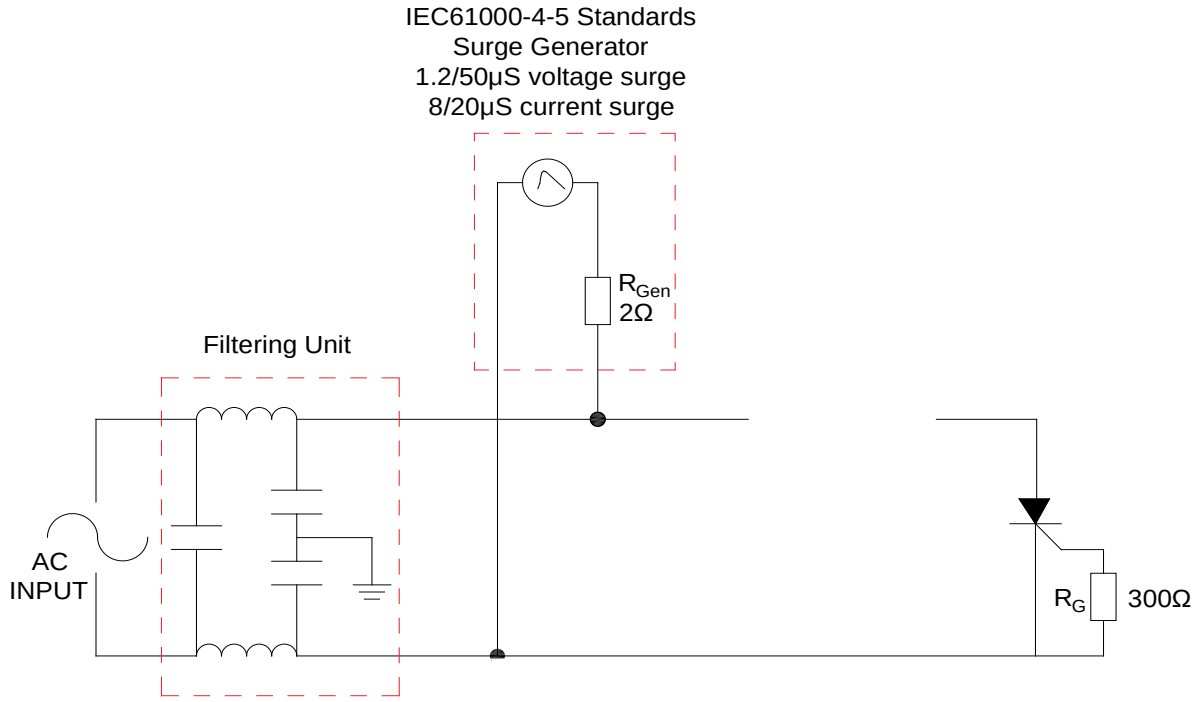
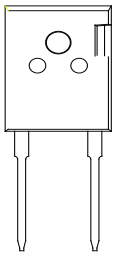
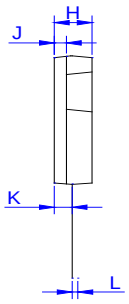


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	





Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50		16.10	0.610		0.634
B1	3.10		3.50	0.122		0.138
C	19.70		20.30	0.776		0.799
D	2.90		3.30	0.114		0.130
E	1.90		2.30	0.075		0.091
F	1.00		1.40	0.039		0.055
G		5.44			0.214	
H	4.80		5.20	0.189		0.205
J	1.90		2.10	0.075		0.083
K	2.20		2.50	0.087		0.098
L	0.41		0.79	0.016		0.031

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